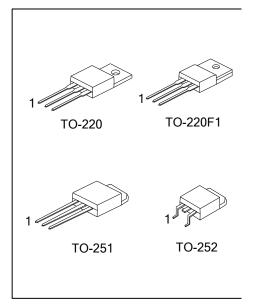
MJE2955T

PNP SILICON TRANSISTOR

HIGH VOLTAGE TRANSISTOR

DESCRIPTION

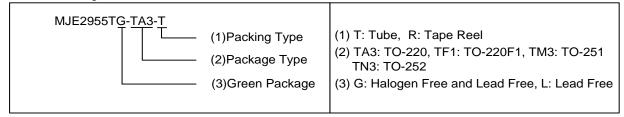
The UTC MJE2955T is designed for general purpose of amplifier and switching applications.



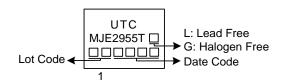
ORDERING INFORMATION

Ordering Number		Daakawa	Pin Assignment			Daakina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MJE2955TL-TA3-T	MJE2955TG-TA3-T	TO-220	В	С	Е	Tube	
MJE2955TL-TF1-T	MJE2955TG-TF1-T	TO-220F1	В	С	Е	Tube	
MJE2955TL-TM3-T	MJE2955TG-TM3-T	TO-251	В	С	Е	Tube	
MJE2955TL-TN3-R	MJE2955TG-TN3-R	TO-252	В	С	Е	Tape Reel	

Note: Pin Assignment: B: Base C: Collector E: Emitter



MARKING



Chunnifying 1688.com www.unisonic.com.tw 1 of 3 QW-R203-012.F

ABSOLUTE MAXIMUM RATING

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V _{CBO}	-70	V
Collector-Emitter Voltage		V_{CEO}	-60	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector current		Ic	-10	Α
Base Current		Ι _Β	-6	Α
Power Dissipation (T _A =25°C)	TO-220	P _D	75	W
	TO-220F1		18	W
	TO-251 TO-252		20	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T _{STG}	-55 ~ + 150	°C

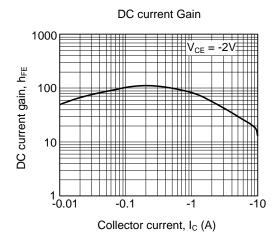
- Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 - 2. The device is guaranteed to meet performance specification within $0^{\circ}\text{C} \sim 70^{\circ}\text{C}$

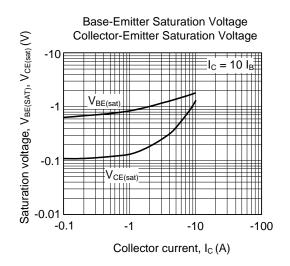
ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

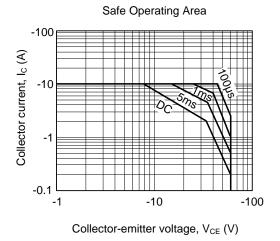
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
				1 11	IVIAA	V	
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-200mA	-60			V	
Collector-Base Breakdown Voltage	BV_CBO	I _C =-10mA	-70			V	
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-10mA	-5			V	
	I _{CBO}	V _{CB} =-70V			-1	mΑ	
Collector Cut-Off Current	I _{CEO}	V _{CE} =-30V			-700	μΑ	
	I _{CEX}	V _{CE} =-70V, V _{EB(OFF)} =-1.5V			-1	mΑ	
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-5V			-5	mΑ	
Collector Emitter Seturation Voltage	V _{CE(SAT)1}	I _C =-4A, I _B =-0.4A			-1.1	V	
Collector-Emitter Saturation Voltage	V _{CE(SAT)2}	I _C =-10A, I _B =-3.3A			-8.0		
Baser-Emitter on Voltage	V _{BE(ON)}	V _{CE} =-4V, I _C =-4A			-1.8	V	
DC Current Gain	h _{FE1}	I _C =-4A, V _{CE} =-4V	20		100		
DC Current Gain	h _{FE2}	I _C =-10A, V _{CE} =-4V	5				
Current Gain Bandwidth Product	f⊤	V _{CE} =-10V, I _C =-0.5A, f=1MHz	2			MHZ	

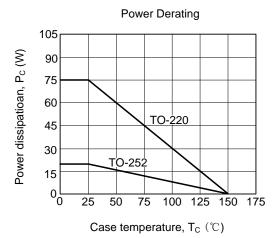


■ TYPICAL CHARACTERISTICS









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